Designator	Value	Description	Footprint
C1, C2	2.2 µF	Capacitor, X6T, ±20%, 2.5 V	0201
C3	10 µF	Capacitor, X6S, ±20%, 6.3 V	0402
C4, C7, C8, C10	100 nF	Capacitor, X7R, ±10%	0201
C5	2.2 nF	Capacitor, X7R, ±10%, 10V	0201
C6	1.5 pF	Capacitor, NP0, ±0.05 pF, 25 V, High Q	0201
C9	2.0 pF	Capacitor, NP0, ±0.05 pF, 25 V	0201
C11	0.3 pF	Capacitor, C0G, ±0.1 pF, 50 V	0201
C12	10 nF	Capacitor, X7R, 6.3 V	0201
C13	3.9 pF	Capacitor, C0G, ±0.25 pF, 50 V	0201
FB1	120 Ω	Ferrite bead, 120 Ω at 100 MHz, 200 mA, 500 mΩ Max	0201
L1	4.7 µH	Inductor, 120 mA, ±20%, 650 mΩ	0603
L2	2.7 nH	Inductor, 600 mA, ±0.1 nH, 120 mΩ	0201
L3, L4	3.5 nH	Inductor, 500 mA, ±0.1 nH, 170 mΩ	0201
R1	1 kΩ	Resistor, ±1%, 0.05 W	0201
U1	nRF54L15-QFAA	Multiprotocol Bluetooth Low Energy, IEEE 802.15.4, and 2.4GHz proprietary System on Chip	QFN-48
X1	32.768 kHz	Crystal SMD 2012, 32.768 kHz, Cl = 9 pF, Total tol: ±20 ppm	XTAL_2012
X2	32 MHz	Crystal SMD 2016, 32 MHz, Cl = 8 pF, Total Tol: ±40 ppm. For frequency tolerance requirements, see 32 MHz crystal oscillator (HFXO) on page 902.	XTAL_2016

Table 87: Bill of material for circuit configuration 1

Note: The antenna filtering components are subject to change.

10.3.2 Circuit configuration 1 for CSP47 (CAAA)

Config no.	Supply configuration		Enabled features
	VDD		NFC
Config 1	DCDC: supplied by battery or external supply		No

Table 88: Circuit configurations

NORDIC®
SEMICONDUCTOR